

TISP4072F3LM THRU TISP4082F3LM, TISP4125F3LM THRU TISP4180F3LM, TISP4240F3LM THRU TISP4380F3LM

BIDIRECTIONAL THYRISTOR OVERVOLTAGE PROTECTORS

TISP4xxxF3LM Overvoltage Protector Series

Ion-Implanted Breakdown Region Precise and Stable Voltage Low Voltage Overshoot under Surge

| Device | V _{DRM} V | V _(BO) |
|--------|-----------------------|-------------------|
| '4072 | 58 | 72 |
| '4082 | 66 | 82 |
| '4125 | 100 | 125 |
| '4150 | 120 | 150 |
| '4180 | 145 | 180 |
| '4240 | 180 | 240 |
| '4260 | 200 | 260 |
| '4290 | 220 | 290 |
| '4320 | 240 | 320 |
| '4380 | 270 | 380 |

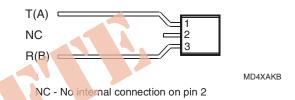
Rated for International Surge Wave Shapes

| Waveshape | Standard | I _{TSP} |
|------------|---------------|------------------|
| 10/160 μs | FCC Part 68 | 60 |
| 0.5/700 μs | l3124 | 38 |
| 10/700 μs | ITU-T K.20/21 | 50 |
| 10/560 μs | FCC Part 68 | 45 |
| 10/1000 μs | REA PE-60 | 35 |

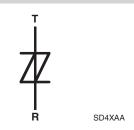
Component

T(A) 1 2 3 MD4XAT NC - No internal connection on pin 2

LMF Package (LM Package with Formed Leads) (Top View)



Device Symbol



Terminals T and R correspond to the alternative line designators of A and B

Description

These devices are designed to limit overvoltages on the telephone line. Overvoltages are normally caused by a.c. power system or lightning flash disturbances which are induced or conducted on to the telephone line. A single device provides 2-point protection and is typically used for the protection of 2-wire telecommunication equipment (e.g. between the Ring to Tip wires for telephones and modems). Combinations of devices can be used for multi-point protection (e.g. 3-point protection between Ring, Tip and Ground).

The protector consists of a symmetrical voltage-triggered bidirectional thyristor. Overvoltages are initially clipped by breakdown clamping until the voltage rises to the breakover level, which causes the device to crowbar into a low-voltage on state. This low-voltage on state causes the current resulting from the overvoltage to be safely diverted through the device. The high crowbar holding current helps prevent d.c. latchup as the diverted current subsides.

How to Order

| Device | Package | Carrier | Order As | | |
|--------------|----------------------------|-----------------|------------------------|--|--|
| TISP4xxxF3LM | Straight Lead DO-92 (LM) | Bulk Pack | TISP4xxxF3LM-S | | |
| | Straight Lead DO-32 (Livi) | Tape and Reeled | Reeled TISP4xxxF3LMR-S | | |
| | Formed Lead DO-92 (LMF) | Tape and Reeled | TISP4xxxF3LMFR-S | | |

Insert xxx value corresponding to protection voltages of 072, 082, 125 etc.

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*RoHS Directive 2002/95/EC Jan 27 2003 including Annex.

Specifications are subject to change without notice.

Customers should verify actual device performance in their specific applications.

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Description (Continued)

This TISP4xxxF3LM range consists of ten voltage variants to meet various maximum system voltage levels (58 V to 270 V). They are guaranteed to voltage limit and withstand the listed international lightning surges in both polarities. These protection devices are supplied in a DO-92 (LM) cylindrical plastic package. The TISP4xxxF3LM is a straight lead DO-92 supplied in bulk pack and on tape and reeled. The TISP4xxxF3LMF is a formed lead DO-92 supplied only on tape and reeled.

Absolute Maximum Ratings, T_A = 25 °C (Unless Otherwise Noted)

| Rating | Symbol | Value | Unit |
|--|---------------------|----------------|------|
| '4072 | | ± 58 | |
| '40a '41a | | ± 66 | |
| | | ± 100 | |
| ·4150 | | ± 120 | |
| Repetitive peak off-state voltage (0 °C < T _{.I} < 70 °C) | VDDM | ± 145 | V |
| 4240 | DRIVI | ± 180 | , |
| '4260 | | ± 200 | |
| 4290 | | ± 220 | |
| 4320 '4380 | | ± 240 ± 270 | |
| Non-repetitive peak on-state pulse current (see Notes 1, 2 and 3) | | | |
| 2/10 us (FCC Part 68, 2/10 us voltage wave shape) excluding '4072 - '4082 | | 175 | |
| 8/20 μs (ANSI C62.41, 1.2/50 μs voltage wave shape) excluding '4072 - '4082 | | 120 | |
| 10/160 us (FCC Part 68, 10/160 us voltage wave shape) | | 60 | |
| 5/200 µs (VDE 0433, 2 kV, 10/700 µs voltage wave shape) | | 50 | |
| 0.2/310 μs (I3124, 1.5 kV, 0.5/700 μs voltage wave shape) | | 38 | |
| 5/310 µs (ITU-T K.20/21, 1.5 kV, 10/700 µs voltage wave shape) | I _{TSP} | 38 | Α |
| 5/310 μs (FTZ R12, 2 kV, 10/700 μs voltage wave shape) | | 50 | |
| 10/560 us (FCC Part 68, 10/560 us voltage wave shape) | | 45 | |
| 10/1000 μs (REA PE-60, 10/1000 μs voltage wave shape) | | 35 | |
| 2/10 µs (FCC Part 68, 2/10 µs voltage wave shape) '4072 - '4082 only | | 80 | |
| 8/20 μs (ANSI C62.41, 1.2/50 μs voltage wave shape) '4072 - '4082 only | | 70 | |
| Non-repetitive peak on-state current (see Notes 2 and 3) | , | 4 | ^ |
| 50/60 Hz, 1 s | ITSM | 4 | Α |
| Initial rate of rise of on-state current, Linear current ramp, Maximum ramp value < 38 A | di _T /dt | 250 | A/μs |
| Junction temperature | T _J | -40 to +150 | °C |
| Storage temperature range | T _{stg} | -55 to +150 | °C |

NOTES: 1. Initially the TISP must be in thermal equilibrium with 0 $^{\circ}C < T_{J} < 70 \ ^{\circ}C.$

- 2. The surge may be repeated after the TISP returns to its initial conditions.
- 3. Above 70 °C, derate linearly to zero at 150 °C lead temperature.

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Electrical Characteristics, T_A = 25 °C (Unless Otherwise Noted)

| | Parameter | Test Conditions | Min | Тур | Max | Unit |
|-------------------|--|---|-------|----------------------------|--|-------|
| I _{DRM} | Repetitive peak off- state current | $V_D = \pm V_{DRM}$, 0 °C < T_J < 70 °C | | | ±10 | μΑ |
| V _(BO) | Breakover voltage | $dv/dt = \pm 250 \text{ V/ms}, R_{SOURCE} = 300 \ \Omega$ '4072 '4082 '4125 '4150 '4180 '4180 '4240 '4260 '4290 '4320 '4380 | | | ±72 ±82 ±125 ±150 ±180 ±240 ±260 ±290 ±320 | V |
| V _(BO) | Impulse breakover voltage | $dv/dt = \pm 1000 \text{ V/}\mu\text{s}, R_{SOURCE} = 50 \ \Omega$ $di/dt < 20 \ \text{A/}\mu\text{s}$ 4320 4380 | | | ±380 ±86 ±96 ±143 ±168 ±198 ±267 ±287 ±317 ±347 ±407 | V |
| I _(BO) | Breakover current | $dv/dt = \pm 250 \text{ V/ms}, R_{SOURCE} = 300 \Omega$ | ±0.15 | | ±0.6 | Α |
| V _T | On-state voltage | $I_T = \pm 5 \text{ A,t }_W = 100 \mu\text{s}$ | | | ±3 | V |
| I _H | Holding current | $T_{T} = \pm 5$ A,d i/dt = -/+ 30 mA/ms | ±0.15 | | | Α |
| dv/dt | Critical rate of rise of off-state voltage | Linear voltage ramp, Maximum ramp value < 0.85V _{DRM} | ±5 | | | kV/μs |
| I _D | Off-state current | $V_D = \pm 50 \text{ V}$ | | | ±10 | μΑ |
| C _{off} | Off-state capacitance | $ \begin{aligned} & \text{f} = 100 \text{ kHz}, & \text{V}_{\text{d}} = 1 \text{ Vr.m.s.,V}_{\text{D}} = 0, & \text{`4072 - `4082} \\ & & \text{`4125 - `4180} \\ & & \text{`4240 - `4380} \\ & \text{f} = 100 \text{ kHz}, & \text{V}_{\text{d}} = 1 \text{ Vr.m.s.,V}_{\text{D}} = -50 \text{ V} & \text{`4072 - `4082} \\ & & \text{`4125 - `4180} \\ & & \text{`4240 - `4380} \end{aligned} $ | | 63 43 44 25 15 | 108 74 74 40 25 20 | pF |

Thermal Characteristics

| Parameter | | arameter Test Conditions | | Тур | Max | Unit |
|-----------------|---|---|--|-----|-----|------|
| $R_{\Theta JA}$ | Junction to free air thermal resistance | EIA/JESD51-3 PCB mounted in an EIA/ JESD51-2 enclosure | | | 120 | °C/W |

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Parameter Measurement Information

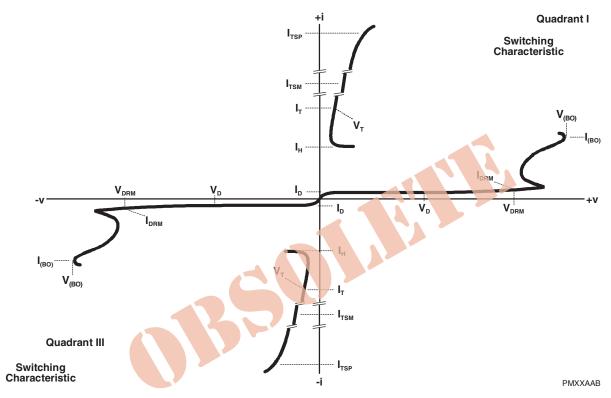
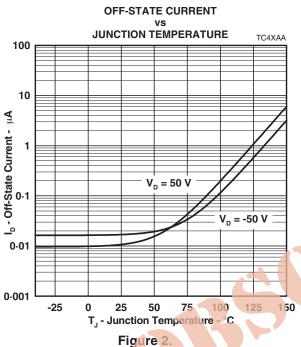
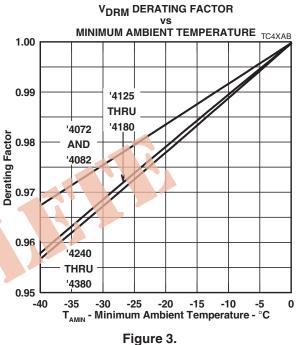


Figure 1. Voltage-Current Characteristic for R and T Terminals

All Measurements are Referenced to the T Terminal

Typical Characteristics





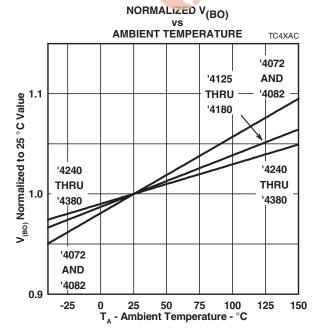
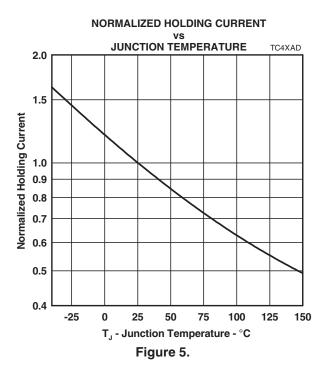
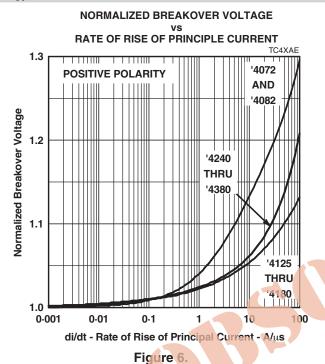


Figure 4.

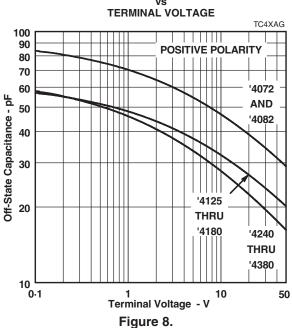
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Typical Characteristics







NORMALIZED BREAKOVER VOLTAGE

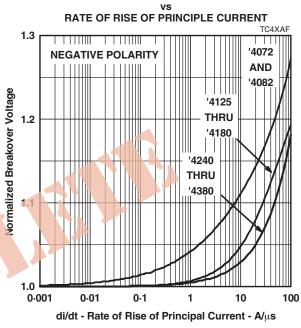
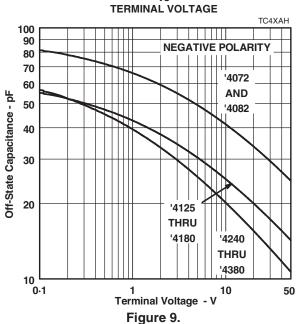


Figure 7.

OFF-STATE CAPACITANCE vs



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Typical Characteristics

NON-REPETITIVE PEAK ON-STATE CURRENT

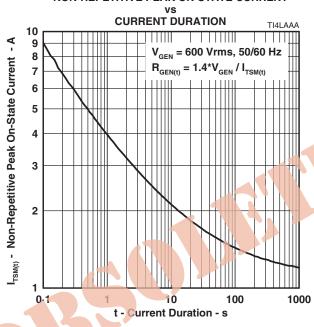


Figure 10.

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MECHANICAL DATA

Device Symbolization Code

Devices will be coded as below.

| Device | Symbolization Code |
|------------|--------------------|
| TISP4072F3 | 4072F3 |
| TISP4082F3 | 4082F3 |
| TISP4125F3 | 4125F3 |
| TISP4150F3 | 4150F3 |
| TISP4180F3 | 4180F3 |
| TISP4240F3 | 4240F3 |
| TISP4260F3 | 4260F3 |
| TISP4290F3 | 4290F3 |
| TISP4320F3 | 4320F3 |
| TISP4380F3 | 4380F3 |

Carrier Information

Devices are shipped in one of the carriers below. A reel contains 2,000 devices.

| Device | Package | Carrier | Order As |
|--------------|------------------------------|-----------------|------------------|
| | Straight Lead DO-92 (LM) | Bulk Pack | TISP4xxxF3LM-S |
| TISP4xxxF3LM | Oli algiti Load DO 32 (Livi) | Tape and Reeled | TISP4xxxF3LMR-S |
| | Formed Lead DO-92 (LMF) | Tape and Reeled | TISP4xxxF3LMFR-S |

Insert xxx value corresponding to protection voltages of 072, 082, 125 etc.